

| | | | | | | konski e i e i. | |
|--|------------------------|---|---|---|---|------------------------------------|---|
| *** | · FXDa | No. 192 & T | ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,, | | | R15 | *** |
| | JA | (Comn | HRU TECHNOI Semester Exam CTRONIC DEV non to EEE, ECE, | inations, Nove VICES AND C | mber/December IRCUITS ETM, MCT) | DERABAD - 2016 ax. Marks: 75 | |
| | | This question paper Part A is compulsor Part B consists of Each question carr | ory which carries of 5 Units. Ans | 25 marks. Answ wer any one f | ver all questions | in Part A. om each unit. | |
| * * * * * * * * * * * * * * * * * * * | | PL | PA | | FIG | (25 Marks) | V * * * * * * * * * * * * * * * * * * * |
| | 1.a) b) c) d) | Define static and d Explain about Zene Define ripple facto Explain about volta | er break down. r. | e of P-N diode. | ericania | [2] [3] [2] [3], | **** |
| | f) g) h) | What are the applic What do you mean Explain about colle Write about therma | cations of UJT? by early effect? ector feedback bial runaway. | | | [2] [3] [2] [3] | # 0 0 X P 1 |
| ************************************** | i) j). | Mention small sign Differentiate betwee | een BJT and JFE | JFΕΤ. Γ | FI | [2] | * # # # # # # # # # # # # # # # # # # # |
| | 2.a) b) | Compare the chara- For a Ge diode, the forward and reverse | ne $I_0=2\mu A$ and the | ne voltage of 0 | .26V is applied. | Calculate the | * |
| | 3.a) b) | Derive an expression Explain Avalanche | on for transition o | capacitance of a | | [5+5] | |
| IÜ. | 4.a) | Explain the operation diagrams. A diode whose inte 110V (R.M.S) sour i) Peak Load Currentii) DC Load Currentii | rnal resistance is ce of supply. Cal nt | 20Ω is to supple culate: | y power to a 100 | ith necessary Ω load from | **** |
| K. *** X X X X X X X X X X X X X X X X X | | iii) AC Load Curre iv) % Regulation fr | om No load to gi | JK | | [\$+5] | 2 A W 4 A W 5 A W 6 A W 6 A W 6 A W 7 A W |
| | b) | Explain the operation A 3K Ω resistive to voltage of adequate filter is used along | oad is to be support magnitude and for the support of the support | olied with a D.C 50Hz frequency Design the blee | C. voltage of 300 by wave rectifice der resistance, | ation. The LC | ···· |
| A 6 9 4 9 9 9 9 8 8 8 8 8 8 8 | ***** | transformer;; VA rat | ing of transform | er and ray raun | g of diodes. | : [ጳ <i>ቪ</i> ጵህ | × 9 4 |



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| :::6;ä) | derive Emitter E | fficiency, Tra | nsport factor and | large signal cur | rent gain and | *** |
|---|--|--------------------------------------|------------------------------------|--|---|---|
| b) | Explain how trans | | | | [5+5] | |
| 7.a) | Explain the opera | | | BJT and its in | out and output | |
| | characteristics brie Explain about Pun | efly. ch through an | nd Base width mod | lulation | [5 +5] | × · · · · · · · · · · · · · · · · · · · |
| 8.a) | What is Biasing? methods. | Explain the | need of it. List | out different ty | pes of biasing | |
| b) | In a Silicon transis | | | • | | |
| | $V_{CC}=9V$, $R_{C}=3K\Omega$ Find the operating | | | | [5+5] | * |
| 9.a) b) | Derive the expressi Explain in detail at | | | | [5+5] | |
| 10.a) b) | Why we call FET a For the Common S i) r _d =100KΩ, R _L =1 | ource Amplif | ier, calculate the v | alue of the voltag | e gain, given | ************************************** |
| | ii) If C _{DS} =3pF, dete | | | | y of 1 MHz. [5+5] | |
| out too) | Define DC Drain | | OR | | | |
| b) | derive them: What are the value 12.4mA and -6V re | es of I_D and , | AC Drain Resistan | * * * * * * * * * * * * * * * * * * * | 111111111111111111111111111111111111111 | A |
| * | derive them: What are the value | es of I_D and , | | * * * * * * * * * * * * * * * * * * * | are given as | |
| * | derive them: What are the value | es of I _D and spectively? | g_m for $V_{GS} = -0.8$ | * * * * * * * * * * * * * * * * * * * | are given as | A |
| b) | derive them: What are the value | es of I _D and spectively? | gm for $V_{GS} = -0.8$ | Wif I _{DSS} and V _I | are given as [5+5] | |
| b) | derive them: What are the value 12.4mA and -6V re | es of I _D and spectively? | gm for $V_{GS} = -0.8$ | W if I _{DSS} and V ₁ | are given as [5+5] | |
| b) | derive them: What are the value 12.4mA and -6V re | es of I _D and spectively? | g _m for $V_{GS} = -0.8$ | W if I _{DSS} and V ₁ | are given as [5+5] | Ħ |